

Patent Abstracts of Japan

PUBLICATION NUMBER : 2001339061
PUBLICATION DATE : 07-12-01

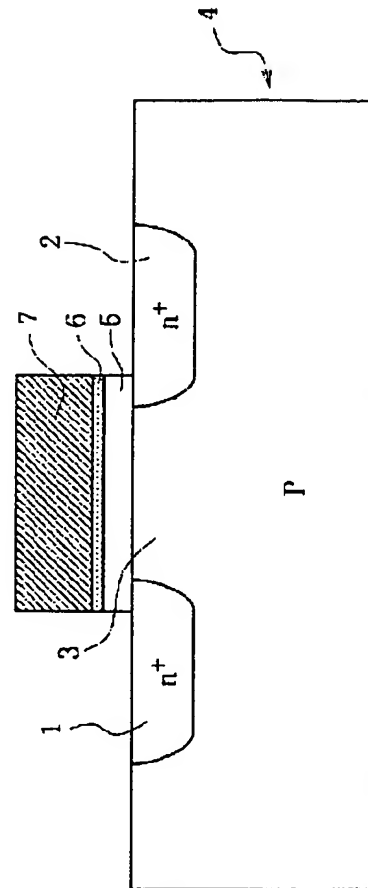
APPLICATION DATE : 30-05-00
APPLICATION NUMBER : 2000159471

APPLICANT : UNIV NAGOYA;

INVENTOR : SAKASHITA MITSUO;

INT.CL. : H01L 29/78 H01L 21/28 H01L 29/43

TITLE : MOS DEVICE AND ITS
MANUFACTURING METHOD



ABSTRACT : PROBLEM TO BE SOLVED: To prevent the mutual conductance and current drive capacity of a MOS transistor from decreasing.

SOLUTION: A carbon compound layer 6 that is disposed between a gate oxide film 5 and a polycrystalline silicon gate electrode 7 prevents an impurity in the polycrystalline silicon gate electrode 7 from proceeding to the gate oxide film 5. As a result, by thinning the gate oxide film 5, gate capacity cannot be decreased remarkably, thus preventing mutual conductance and current drive capacity from decreasing.

COPYRIGHT: (C)2001,JPO